

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (previously presented) A method of combining components to form an integrated device, comprising the following steps:

- providing at least one first component on a first surface of a sacrificial substrate,

- providing at least one second component on a first surface of a non-sacrificial substrate;

- forming at least one support structure on at least one of said first surfaces of said sacrificial substrate, and said non-sacrificial substrate, respectively, such that said at least one support structure is extended outwardly from at least one of said first surfaces;

- bonding said sacrificial substrate carrying said at least one first component, and said non-sacrificial substrate carrying said at least one second component, respectively, with an intermediate bonding material, so that said first surfaces will be facing one another with a distance essentially defined by a thickness of said support structure,

- removing at least a part of said sacrificial substrate;

- mechanically and/or electrically interconnecting said at least one first component and said at least one second component.

2. (original) The method according to claim 1, further comprising the action of:

- patterning said at least one first component after bonding said sacrificial substrate with said non-sacrificial substrate.

3. (original) The method according to claim 1, further comprising the action of:

- arranging a metal layer on a first surface of said at least one first component facing away from said non-sacrificial substrate after said bonding.

4. (previously presented) The method according to claim 3, further comprising the action of:

- arranging a metal layer on a second surface of said at least one first component facing said non-sacrificial substrate prior to said bonding.

5. (previously presented) The method according to claim 1 comprising the action of:

- doping at least one first component made of semiconducting material and facing said non-sacrificial substrate prior to said bonding.

6. (previously presented) The method according to claim 4, wherein said metal layers on said first and second surfaces of said first component are of equivalent thickness.

7. (original) The method according to claim 1, further comprising the action of:

- providing at least one additional layer of stress compensating material on said first component.

8. (previously presented) The method according to claim 7, wherein said stress compensating material is at least one of the materials of: SiO₂, SiN, metal.

9. (original) The method according to claim 1, further comprising the action of:

- performing said interconnection of said at least one second component with said at least one first component with the help of said at least one support structure.

10. (previously presented) The method according to claim 1, further comprising the action of:

- securing said at least one first component to said non-sacrificial substrate with means other than said intermediate bonding material.

11. (original) The method according to claim 10, further comprising the action of:

- stripping away said intermediate bonding material.

12. (original) The method according to claim 1, wherein said support structure is made of electrically non conducting material.

13. (original) The method according to claim 1, wherein said support structure is made of electrically conducting material.

14. (original) The method according to claim 12, further comprising the action of:

- depositing an electrically conducting material on at least a portion of a surface of said support structure, prior to said bonding, for forming an electrical connection between said at least one first component and said at least one second component.

15. (previously presented) The method according to claim 1, further comprising the action of securing said at least one first component to said non-sacrificial substrate and said interconnection of said at least one first component with said at least one second component in a single action.

16. (previously presented) The method according to claim 1, wherein said first component and said non-sacrificial substrate are secured to each other by one of the group of: evaporation, spin coating, sputtering, plating, riveting, soldering, gluing.

17. (previously presented) The method according to claim 1, wherein said intermediate bonding material is a low

temperature adhesive polymer selected from poly-imide, bensocyclobutene (BCB), epoxy, photoresist.

18. (original) The method according to claim 2, wherein said first component is a micro mirror.

19. (original) The method according to claim 1, wherein said first component is made of single crystalline material.

20. (original) The method according to claim 19, wherein said first component is made of single crystalline semiconducting material.

21. (original) The method according to claim 1, wherein said second component is an integrated circuit.

22. (original) The method according to claim 1, wherein said integrated device is a micro mirror Spatial Light Modulator (SLM).

23. (original) The method according to claim 1, wherein said support structure is hollow with an open end.

24. (original) The method according to claim 1, further comprising the action of:

- forming said support structure lithographically by patterning the intermediate bonding material prior to bonding.

25. (previously presented) The method according to claim 1, wherein said second component is at least partly prefabricated prior to bonding.

26. (currently amended) A Spatial Light Modulator comprising:

a substrate with at least one integrated circuit;

a plurality of micro mirror modulating elements that are individually movable reflecting elements to which hinge elements are attached, said reflecting elements being made of single crystalline material;

support members defining a spacing between said substrate and said modulating elements; and

interconnecting [[metal]] elements that electrically interconnect said modulating elements and said substrate.

27-30. (canceled)

31. (previously presented) The method according to claim 1, further comprising the action of:

- arranging a metal layer on a second surface of said at least one first component facing said non-sacrificial substrate prior to said bonding.

32. (previously presented) The Spatial Light Modulator of claim 26, wherein said single crystalline material is selected from the group consisting of single crystalline silicon, single crystalline silicon germanium, single crystalline germanium, single crystalline gallium arsenide, single crystalline indium phosphate, and single crystalline silicon carbide.

33. (previously presented) The Spatial Light Modulator of claim 26, wherein said support members are at least partly coated with an electrically conducting material.

34. (previously presented) The Spatial Light Modulator of claim 26, wherein said hinge elements comprise torsion or flexible members.

35. (currently amended) A Spatial Light Modulator comprising:

a substrate with at least one integrated circuit;

a plurality of micro mirror modulating elements that are individually movable reflecting elements to which hinge elements are attached, said reflecting elements being made of one or more materials selected from the group consisting of high temperature annealed and high temperature deposited material;

support members defining a spacing between said substrate and said modulating elements; and

interconnecting [[metal]] elements that electrically interconnect said modulating elements and said substrate.